



Shantou Huashan Electronic Devices Co.,Ltd.

NPN DIGITAL TRANSISTOR

HC114Y

APPLICATIONS

Switching Circuit , Interface Circuit.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature..... -55~150

T_j —Junction Temperature..... 150

P_C —Collector Dissipation..... 300mW

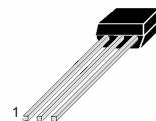
V_{CBO} —Collector-Base Voltage..... 50V

V_{CEO} —Collector-Emitter Voltage..... 50V

V_{EBO} —Emitter-Base Voltage..... 6V

I_C —Collector Current..... 100mA

TO-92S



- 1 Emitter , E
- 2 Collector , C
- 3 Base , B

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	50			V	$I_C=10 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	50			V	$I_C=1mA, I_B=0$
I_{CBO}	Collector Cut-off Current			0.1	μA	$V_{CB}=40V, I_E=0$
I_{CEO}	Collector Cut-off Current			0.5	μA	$V_{CE}=40V, I_B=0$
I_{EBO}	Emitter Cut-off Current	67	88	125	μA	$V_{EB}=5V, I_C=0$
HFE	DC Current Gain	70				$V_{CE}=5V, I_C=5mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.1	0.3	V	$I_C=10mA, I_B=0.5mA$
$V_I(\text{off})$	Input Off Voltage	0.5	0.7	0.9	V	$V_{CE}=5V, I_C=0.1mA$
$V_I(\text{on})$	Input On Voltage	0.7	1.0	2.0	V	$V_{CE}=0.2V, I_C=5mA$
R_1	Input Resistor	7.0	10	13	Kohm	
R_1/ R_2	Resistor Ratio	0.193	0.213	0.234		
f_T	Current Gain-Bandwidth Product		250		MHz	$V_{CE}=10V, I_C=5mA$
C_{ob}	Output Capacitance		3.7		pF	$V_{CB}=10V, f=1MHz$



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●Electrical characteristic curves

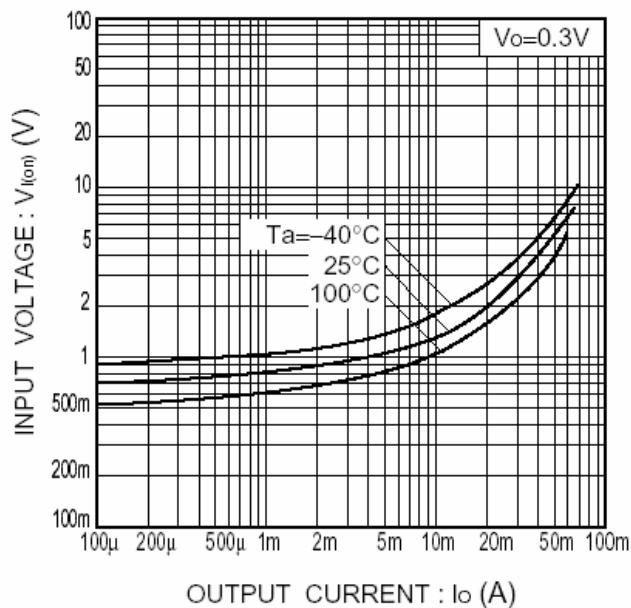


Fig.1 Input voltage vs. output current
(ON characteristics)

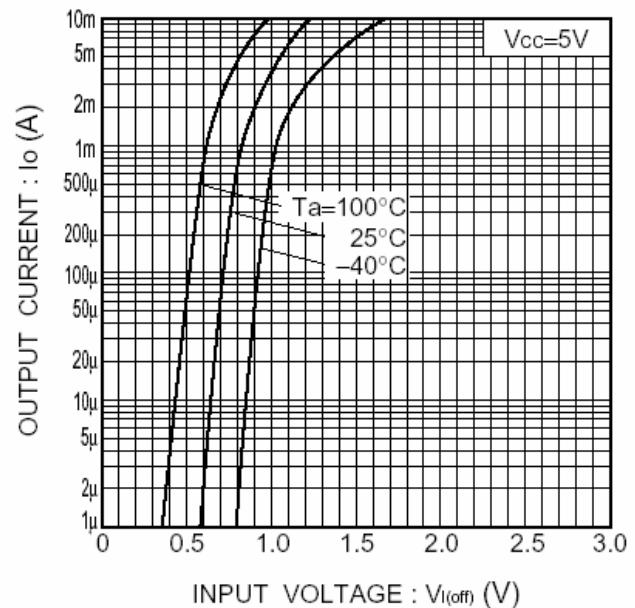


Fig.2 Output current vs. input voltage
(OFF characteristics)

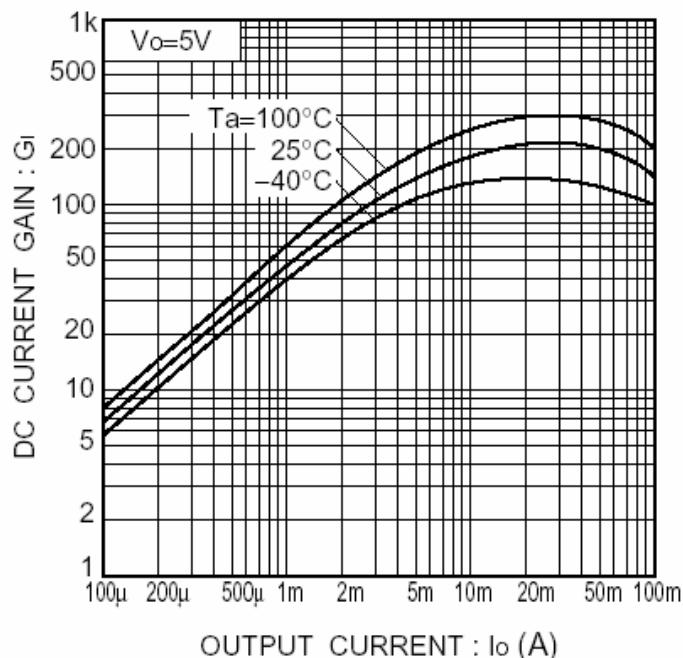


Fig.3 DC current gain vs. output current

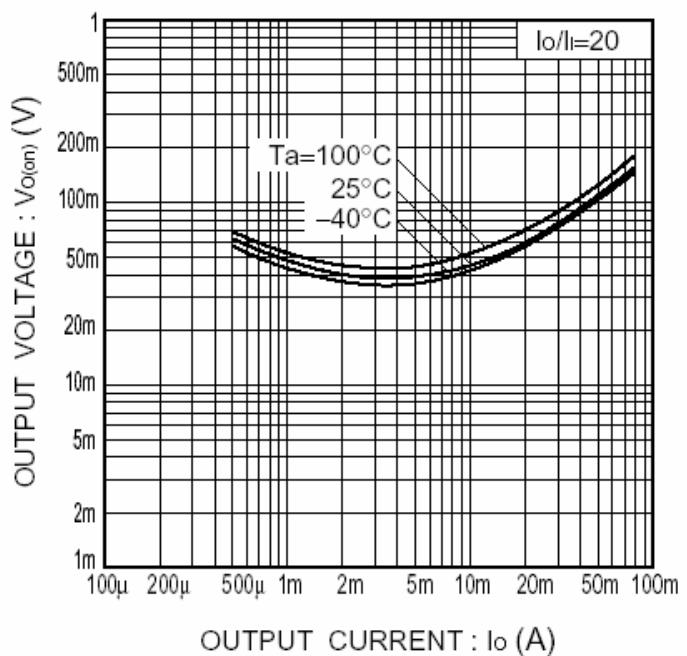


Fig.4 Output voltage vs. output current